

L Number	Hits	Search Text	DB	Time stamp
-	1229	(soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 11:58
-	1079	((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20010425	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:42
-	900	((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20000406	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:42
-	311	((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20000406) and (silicide cobalt co titanium ti)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:45
-	90939	((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20000406) and (silicide cobalt co titanium ti) implant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:43
-	12	((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20000406) and (silicide cobalt co titanium ti) with implant	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:43
-	254	((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20000406) and (silicide cobalt co titanium ti) and source and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:54
-	14	((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20000406) and (silicide cobalt co titanium ti) and source and drain) and ratio with silicon	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:55
-	3	("5801084" "6096582" "6159824").PN.	USPAT	2002/12/11 13:58
-	6	oki.as. and (soi with fet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 13:59
-	2	("6190977" "6287901").PN.	USPAT	2002/12/11 14:01
-	1794	soi and fet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:18
-	161	(soi and fet) and ((source drain) with silicide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:19
-	102	((soi and fet) and ((source drain) with silicide)) and @ad<=20000406	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:24

-	2	(((soi and fet) and ((source drain) with silicide)) and @ad<=20000406) and silicide with ratio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:27
-	2	(((soi and fet) and ((source drain) with silicide)) and @ad<=20000406) and (refractory metal) with (rich stuffed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:28
-	2	(((soi box (silicon adj on adj insulator) (buried adj oxide)) with (fet (field adj effect adj transistor))) and @ad<=20000406) and (refractory metal) with (rich stuffed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:28
-	7899	(refractory metal) with (rich stuffed)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:28
-	653	((refractory metal) with (rich stuffed)) and ((438/\$(257/\$(ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:30
-	71	(((refractory metal) with (rich stuffed)) and ((438/\$(257/\$(ccls.) and fet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:30
-	19	(((refractory metal) with (rich stuffed)) and ((438/\$(257/\$(ccls.) and fet) and soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:38
-	8	("5288948") or ("6037588") or ("6197601") or ("6274470").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 15:06
-	1	6274470.URPN.	USPAT	2002/12/11 14:40
-	2	(drain source) with silicide and stuff\$3 with (refractory metal)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:42
-	899	(drain source) with silicide and fet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:43
-	161	((drain source) with silicide and fet) and soi	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:43
-	102	(((drain source) with silicide and fet) and soi) and @ad<=20000406	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 14:43
-	7	5719083.URPN.	USPAT	2002/12/11 14:45
-	7	5719083.URPN.	USPAT	2002/12/11 14:45

-	10	("3830657" "5084413" "5087296" "5094697" "5112773" "5177569" "5198389" "5254481" "5445982" "5554566").PN.	USPAT	2002/12/11 14:45
-	1	6274470.URPN.	USPAT	2002/12/11 14:54
-	5	("5869396" "6022457" "6025267" "6083817" "6274470").PN.	USPAT	2002/12/11 14:54
-	2	6022457.URPN.	USPAT	2002/12/11 14:59
-	14	("4378628" "4814294" "5045496" "5047367" "5356837" "5449642" "5536684" "5567651" "5736461" "5874342" "5902129" "5904564" "5989988" "6022457").PN.	USPAT	2002/12/11 15:00
-	14	((cobalt with rich) with silicide and ((438/\$) (257/\$)).ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/11 15:09
-	64	4378628.URPN.	USPAT	2002/12/11 15:14
-	4331	((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:25
-	521	((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:26
-	249	(((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:26
-	199	(((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode) and @ad<=20000406	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:39
-	0	((((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode) and @ad<=20000406) and "co.sub.2si"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:39
-	1	((((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode) and @ad<=20000406) and cobalt with rich	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:40
-	2	((((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode) and @ad<=20000406) and cobalt with excess	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 07:41
-	71	((((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode) and @ad<=20000406) and silicide with low with resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 08:24
-	1	((((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode) and @ad<=20000406) and silicide with low with resistance) and (dicobalt (di adj cobalt))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 08:24

-	118	((((438/476) or (438/655) or (438/656) or (438/664) or (438/683) or (438/685)).CCLS.) and (cobalt)) and (source drain) and electrode) and @ad<=20000406) and low with resistance	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 13:59
-	12	"cobalt monosilicide" and stable	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:02
-	3	"cobalt monosilicide" and unstable	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:02
-	47	"cobalt monosilicide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/13 14:08
-	47	"cobalt monosilicide"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/14 10:40
-	18	"cobalt monosilicide" and (ratio stoichiometric\$3)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/12/14 10:40
-	1492	(soi box (silicon adj on adj insulator) (buried adj oxide) simox) with (fet (field adj effect adj transistor))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/21 11:58
-	1060	(soi box (silicon adj on adj insulator) (buried adj oxide) simox) with (fet (field adj effect adj transistor))	USPAT; US-PGPUB	2003/09/21 11:58
-	319	((soi box (silicon adj on adj insulator) (buried adj oxide) simox) with (fet (field adj effect adj transistor))) and silicide	USPAT; US-PGPUB	2003/09/21 12:09
-	31	((soi box (silicon adj on adj insulator) (buried adj oxide) simox) with (fet (field adj effect adj transistor))) and silicide with (bottom rear)	USPAT; US-PGPUB	2003/09/21 12:09
-	1	"5883396".PN.	USPAT	2003/09/21 12:55
-	1	6160293.URPN.	USPAT	2003/09/21 12:55
-	14	("4617066" "5710450" "5965917" "6087234" "6121100" "6160291" "6160293" "6165826" "6274488" "6316357" "6335253" "6380590" "6395587" "6403433").PN.	USPAT	2003/09/21 12:55